

Andrzej WysmoÅek

List of Publications by Year in descending order

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165
papers

2,892
citations

218381

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165
all docs

165
docs citations

165
times ranked

3566
citing authors

#	ARTICLE	IF	CITATIONS
1	Strain control in graphene on GaN nanowires: Towards pseudomagnetic field engineering. Carbon, 2022, 186, 128-140.	5.4	1
2	Enhancement of graphene-related and substrate-related Raman modes through dielectric layer deposition. Applied Physics Letters, 2022, 120, .	1.5	9
3	Raman Optical Activity of 1T-TaS ₂ . Nano Letters, 2022, 22, 2835-2842.	4.5	10
4	Importance of catalystâ€“photoabsorber interface design configuration on the performance of Mo-doped BiVO ₄ water splitting photoanodes. Journal of Solid State Electrochemistry, 2021, 25, 173-185.	1.2	2
5	Low-strain sensor based on the flexible boron-doped diamond-polymer structures. Carbon, 2021, 173, 832-841.	5.4	13
6	Free Excitonic Emission in Homoepitaxial Layers Grown on Bulk GaN Substrates. Acta Physica Polonica A, 2021, 139, 300-303.	0.2	0
7	Charge Transfer in 1T-TaS ₂ /Graphene Hybrid Structures Studied by Spatially Resolved Raman Spectroscopy. Acta Physica Polonica A, 2021, 139, 311-313.	0.2	0
8	Delamination of Large Area Layers of Hexagonal Boron Nitride Grown by MOVPE. Acta Physica Polonica A, 2021, 139, 457-461.	0.2	4
9	Suspended graphene on germanium: selective local etching via laser-induced photocorrosion of germanium. 2D Materials, 2021, 8, 035043.	2.0	3
10	Properties of graphene deposited on GaN nanowires: influence of nanowire roughness, self-induced nanogating and defects. Beilstein Journal of Nanotechnology, 2021, 12, 566-577.	1.5	3
11	Towards practical applications of quantum emitters in boron nitride. Scientific Reports, 2021, 11, 15506.	1.6	6
12	Stable Field Electron Emission and Plasma Illumination from Boron and Nitrogen Coâ€“Doped Edgeâ€“Rich Diamondâ€“Enhanced Carbon Nanowalls. Advanced Materials Interfaces, 2021, 8, 2100464.	1.9	9
13	Highly effective gating of graphene on GaN. Applied Surface Science, 2021, 560, 149939.	3.1	3
14	Photoluminescence as a probe of phosphorene properties. Npj 2D Materials and Applications, 2021, 5, .	3.9	11
15	Optical properties of N-polar GaN: The possible role of nitrogen vacancy-related defects. Applied Surface Science, 2021, 566, 150734.	3.1	8
16	Two stage epitaxial growth of wafer-size multilayer h-BN by metal-organic vapor phase epitaxy â€“ a homoepitaxial approach. 2D Materials, 2021, 8, 015017.	2.0	20
17	Heteroepitaxial Growth of High Optical Quality, Wafer-Scale van der Waals Heterostructures. ACS Applied Materials & Interfaces, 2021, 13, 47904-47911.	4.0	14
18	Impeded phase transition in 1T-TaS ₂ : Thermoelectric fingerprint of long-lived mixed states. Solid State Communications, 2020, 305, 113749.	0.9	9

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19	In-situ monitoring of electropolymerization processes at boron-doped diamond electrodes by Mach-Zehnder interferometer. <i>Sensors and Actuators B: Chemical</i> , 2020, 304, 127315.	4.0	4
20	Tuning Light-Driven Water Oxidation Efficiency of Molybdenum-Doped BiVO ₄ by Means of Multicomposite Catalysts Containing Nickel, Iron, and Chromium Oxides. <i>ChemPlusChem</i> , 2020, 85, 327-333.	1.3	6
21	Spatially resolved thermoelectric response of mixed states. , 2020, , .		0
22	Anomalous size effect in thermal residual stresses in pressure sintered alumina-chromium composites. <i>Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 2019, 762, 138111.	2.6	5
23	Upconverted electroluminescence via Auger scattering of interlayer excitons in van der Waals heterostructures. <i>Nature Communications</i> , 2019, 10, 2335.	5.8	51
24	Optical measurements of thermal residual stresses in alumina reinforced with chromium. <i>Journal of Applied Physics</i> , 2019, 125, 135104.	1.1	5
25	STS observations of deep defects within laser-illuminated graphene/MOPE-h-BN heterostructures. <i>Applied Physics Letters</i> , 2019, 114, .	1.5	3
26	Surface-enhanced Raman scattering in graphene deposited on Al Ga ^{1~N} /GaN axial heterostructure nanowires. <i>Applied Surface Science</i> , 2019, 475, 559-564.	3.1	7
27	An Influence of X-Ray Irradiation on Mid-Bandgap Luminescence of Boron Nitride Epitaxial Layers. <i>Acta Physica Polonica A</i> , 2019, 136, 620-623.	0.2	0
28	Raman scattering from the bulk inactive out-of-plane $B_{2g}^{(1)}$ mode in few-layer MoTe ₂ . <i>Scientific Reports</i> , 2018, 8, 17745.	1.6	12
29	Electronic structure of commensurate, nearly commensurate, and incommensurate phases of S_2 by angle-resolved photoelectron spectroscopy, scanning tunneling spectroscopy, and density functional theory. <i>Physical Review B</i> , 2018, 98, .	1.1	29
30	Laser-controlled field effect in graphene/hexagonal boron nitride heterostructures. <i>Journal of Applied Physics</i> , 2018, 123, .	1.1	3
31	X-ray and Raman determination of InAsSb mole fraction for $x \leq 0.5$. <i>Journal of Crystal Growth</i> , 2018, 498, 137-139.	0.7	3
32	Surface-enhanced Raman scattering of graphene caused by self-induced nanogating by GaN nanowire array. <i>Carbon</i> , 2018, 128, 70-77.	5.4	8
33	Anomalous Raman Scattering In Few Monolayer MoTe ₂ . <i>MRS Advances</i> , 2017, 2, 1539-1544.	0.5	1
34	Resonant quenching of Raman scattering due to out-of-plane A_{1g} modes in few-layer MoTe ₂ . <i>Nanophotonics</i> , 2017, 6, 1281-1288.	2.9	16
35	In Situ Raman Spectroscopy of Solution-Gated Graphene on Copper. <i>Acta Physica Polonica A</i> , 2017, 132, 360-363.	0.2	1
36	Raman and photoluminescence investigation of InAs/GaSb and InAs/InAsSb superlattices. , 2017, , .		0

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37	Raman scattering of few-layers MoTe ₂ . 2D Materials, 2016, 3, 025010.	2.0	67
38	<i>In situ</i> Raman spectroscopy of the graphene/water interface of a solution-gated field-effect transistor: electron-phonon coupling and spectroelectrochemistry. Nanotechnology, 2016, 27, 045704.	1.3	9
39	Structural and Optical Properties of Boron Nitride Grown by MOVPE. Acta Physica Polonica A, 2016, 129, A-129-A-131.	0.2	3
40	Raman Spectroscopy of Shear Modes in a Few-Layer MoS ₂ . Acta Physica Polonica A, 2016, 129, A-132-A-134.	0.2	3
41	Light Induced Modification of Graphene Oxide Layers on GaN Basis. Acta Physica Polonica A, 2016, 130, 1169-1171.	0.2	1
42	Strong Photoluminescence Fluctuations in Laser-Thinned Few-Layer WS ₂ . Acta Physica Polonica A, 2016, 130, 1176-1178.	0.2	3
43	Enhanced Raman scattering and weak localization in graphene deposited on GaN nanowires. Physical Review B, 2015, 92, .	1.1	9
44	The disorder-induced Raman scattering in Au/MoS ₂ heterostructures. AIP Advances, 2015, 5, .	0.6	27
45	Electron scattering in graphene with adsorbed NaCl nanoparticles. Journal of Applied Physics, 2015, 117, 014308.	1.1	3
46	A micro-magneto-Raman scattering study of graphene on a bulk graphite substrate. Europhysics Letters, 2014, 108, 27011.	0.7	6
47	Dynamics of stacking faults luminescence in GaN/Si nanowires. Journal of Luminescence, 2014, 155, 293-297.	1.5	24
48	Resonant Raman scattering in MoS ₂ – From bulk to monolayer. Solid State Communications, 2014, 197, 53-56.	0.9	108
49	Graphene Based Flow Sensors. Acta Physica Polonica A, 2014, 126, 1209-1212.	0.2	1
50	Optical and Electrical Studies of Graphene Deposited on GaN Nanowires. Acta Physica Polonica A, 2014, 126, 1087-1089.	0.2	0
51	ESR Spectroscopy of Graphene with Adsorbed NaCl Particles. Acta Physica Polonica A, 2014, 126, 1187-1189.	0.2	1
52	Nitrogen doping of chemical vapor deposition grown graphene on 4H-SiC (0001). Journal of Applied Physics, 2014, 115, .	1.1	27
53	Multiphonon resonant Raman scattering in MoS ₂ . Applied Physics Letters, 2014, 104, 092106.	1.5	118
54	Dynamics of thermalization in GaInN/GaN quantum wells grown on ammonothermal GaN. Journal of Applied Physics, 2013, 114, .	1.1	14

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55	Optical Properties of Molybdenum Disulfide (MoS ₂). Acta Physica Polonica A, 2013, 124, 849-851.	0.2	42
56	Enhancement of elastic and inelastic scattering lengths in quasi-free-standing graphene measured with contactless microwave spectroscopy. Physical Review B, 2013, 88, .	1.1	9
57	Fine optical spectroscopy of the 3.45 eV emission line in GaN nanowires. Journal of Applied Physics, 2013, 113, 043102.	1.1	28
58	Photon correlation studies of charge variation in a single GaAlAs quantum dot. Physical Review B, 2013, 87, .	1.1	20
59	Micro-Raman spectroscopy of graphene grown on stepped 4H-SiC (0001) surface. Applied Physics Letters, 2012, 100, .	1.5	27
60	Pinned and unpinned epitaxial graphene layers on SiC studied by Raman spectroscopy. Journal of Applied Physics, 2012, 111, .	1.1	14
61	Graphene Epitaxy by Chemical Vapor Deposition on SiC. Nano Letters, 2011, 11, 1786-1791.	4.5	296
62	Carrier Scattering from Dynamical Magnetoconductivity in Quasineutral Epitaxial Graphene. Physical Review Letters, 2011, 107, 216603.	2.9	57
63	Anharmonic Optical Phonon Effects in ZnO Nanocrystals. Acta Physica Polonica A, 2011, 119, 678-680.	0.2	3
64	Absorption and Emission Properties of Light Emitting Diode Structures Containing GaInN/GaN QWs. Acta Physica Polonica A, 2011, 120, 918-920.	0.2	1
65	Built-In Electric Field in High Quality GaN/AlGaIn Quantum Wells. Acta Physica Polonica A, 2011, 119, 657-659.	0.2	0
66	Raman Studies of Defects in Graphene Grown on SiC. Acta Physica Polonica A, 2011, 119, 595-596.	0.2	0
67	Growth kinetics of epitaxial graphene on SiC substrates. Physical Review B, 2010, 81, .	1.1	26
68	Electroreflectance investigations of quantum confined Stark effect in GaN quantum wells. Journal of Physics: Conference Series, 2010, 253, 012009.	0.3	0
69	Transmission electron microscopy investigations of epitaxial graphene on C-terminated 4H-SiC. Journal of Applied Physics, 2010, 108, .	1.1	35
70	Quasiclassical cyclotron resonance of Dirac fermions in highly doped graphene. Physical Review B, 2010, 82, .	1.1	86
71	Transmission electron microscopy and scanning tunneling microscopy investigations of graphene on 4H-SiC(0001). Journal of Applied Physics, 2009, 105, .	1.1	57
72	1.4 eV - LUMINESCENCE BAND IN 6H-SiC: SYMMETRY OF THE ASSOCIATED DEFECT. International Journal of Modern Physics B, 2009, 23, 3019-3023.	1.0	1

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73	MAGNETO-LUMINESCENCE OF GADOLINIUM DOPED GALLIUM NITRIDE. International Journal of Modern Physics B, 2009, 23, 2994-2998.	1.0	1
74	TEM Investigations of Graphene on 4H-SiC(0001). Materials Science Forum, 2009, 615-617, 207-210.	0.3	0
75	Optical Absorption and Raman Scattering Studies of Few-Layer Epitaxial Graphene Grown on 4H-SiC Substrates. Acta Physica Polonica A, 2009, 116, 835-837.	0.2	5
76	Raman Piezospectroscopy of Phonons in Bulk 6H-SiC. Acta Physica Polonica A, 2009, 116, 947-949.	0.2	5
77	Time Evolution of the Microluminescence Energy \hat{I}_2^f GaN/AlGaN Quantum Dots. Acta Physica Polonica A, 2009, 116, 933-935.	0.2	0
78	Ammonothermal synthesis of GaN doped with transition metal ions (Mn, Fe, Cr). Journal of Alloys and Compounds, 2008, 456, 324-338.	2.8	56
79	Time-Resolved Studies of Gallium Nitride Doped with Gadolinium. Acta Physica Polonica A, 2008, 114, 1425-1430.	0.2	2
80	Time Resolved Magnetophotoluminescence of Biased GaAs/AlGaAs Double Quantum Well Structure. Acta Physica Polonica A, 2008, 114, 1369-1374.	0.2	0
81	Transmission Electron Microscopy and Luminescence Studies of Quantum Well Structures Resulting from Stacking Fault Formation in 4H-SiC Layers. Acta Physica Polonica A, 2008, 114, 1067-1072.	0.2	0
82	DIRECT BANDGAP QUANTUM DOTS EMBEDDED IN A TYPE-II GaAs/AlAs DOUBLE QUANTUM WELL STRUCTURE. International Journal of Modern Physics B, 2007, 21, 1654-1658.	1.0	4
83	MAGNETOPOLARON EFFECT ON SILICON AND OXYGEN DONORS IN GAN. International Journal of Modern Physics B, 2007, 21, 1486-1490.	1.0	0
84	Diluted Magnetic III-V Semiconductors With Mn For Possible Spintronic Applications. AIP Conference Proceedings, 2007, , .	0.3	0
85	Magneto-spectroscopy of donor-bound excitons in GaN. Physica B: Condensed Matter, 2007, 401-402, 441-446.	1.3	3
86	Magneto-optical studies of iron impurity in HVPE GaN. Physica B: Condensed Matter, 2007, 401-402, 458-461.	1.3	3
87	Control of Photon Polarization in GaAs/AlAs Single Quantum Dot Emission. Acta Physica Polonica A, 2007, 112, 461-466.	0.2	4
88	Magnetized Plasma in Polar Semiconductors. Acta Physica Polonica A, 2007, 112, 141-152.	0.2	0
89	Single GaN/AlGaN Quantum Dot Spectroscopy. Acta Physica Polonica A, 2007, 112, 233-236.	0.2	0
90	Magnetoluminescence Studies of GaN:Fe. Acta Physica Polonica A, 2007, 112, 177-182.	0.2	0

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91	Coupling of phonons with excitons bound to different donors and acceptors in hexagonal GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 1940-1943.	0.8	3
92	Low density GaN quantum dots on AlGaIn. <i>Physica Status Solidi (B): Basic Research</i> , 2006, 243, 1486-1489.	0.7	8
93	Growth of low-density GaN quantum dots on Al _x Ga _{1-x} N. <i>Journal of Crystal Growth</i> , 2006, 289, 472-476.	0.7	6
94	Manganese as a fast charge carrier trapping center in InP. <i>Physica B: Condensed Matter</i> , 2006, 382, 220-228.	1.3	10
95	Coupled plasmon-LO-phonon modes at high-magnetic fields. <i>Physical Review B</i> , 2006, 74, .	1.1	13
96	Magnetopolaron effect on shallow donors in GaN. <i>Physical Review B</i> , 2006, 74, .	1.1	7
97	Photoluminescence and Electron Paramagnetic Resonance Studies of Bulk GaN Doped with Gadolinium. <i>Acta Physica Polonica A</i> , 2006, 110, 243-248.	0.2	14
98	Magneto-Luminescence Study of Silicon-Vacancy in 6H-SiC. <i>Acta Physica Polonica A</i> , 2006, 110, 437-442.	0.2	2
99	Dynamics of ground and excited states of bound excitons in gallium nitride. <i>Journal of Luminescence</i> , 2005, 112, 30-33.	1.5	4
100	Anomalous behaviour of the photoluminescence from GaN/AlGaIn quantum wells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 1010-1013.	0.8	2
101	Recombination dynamics in GaN/AlGaIn low dimensional structures obtained by SiH ₄ treatment. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 1069-1072.	0.8	0
102	Neutral Mn Acceptor in GaN Studied in High Magnetic Fields. <i>AIP Conference Proceedings</i> , 2005, , .	0.3	0
103	Photoluminescence Study of Bulk GaN Doped with Beryllium. <i>Acta Physica Polonica A</i> , 2005, 108, 705-710.	0.2	4
104	Carriers Diffusion in GaAs/AlAs Type II Quantum Well. <i>Acta Physica Polonica A</i> , 2005, 108, 755-760.	0.2	2
105	MAGNETO-LUMINESCENCE OF A SINGLE LATERAL ISLAND FORMED IN A TYPE - II GaAs/AlAs QW. , 2005, , .		0
106	Temporal Evolution of Multi-Carrier Complexes in Single GaN/AlGaIn Quantum Dots. <i>Acta Physica Polonica A</i> , 2005, 108, 879-884.	0.2	1
107	Reply to "Comment on "Recombination of excitons bound to oxygen and silicon donors in freestanding GaN" Physical Review B, 2004, 69, .	1.1	7
108	Neutral Mn acceptor in bulk GaN in high magnetic fields. <i>Physical Review B</i> , 2004, 70, .	1.1	54

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109	MAGNETO-LUMINESCENCE OF A SINGLE LATERAL ISLAND FORMED IN A TYPE - II GaAs/AlAs QW. International Journal of Modern Physics B, 2004, 18, 3807-3812.	1.0	2
110	Electronic structure of shallow impurities in GaN studied via bound exciton magnetooptics. Physica Status Solidi A, 2004, 201, 181-189.	1.7	4
111	Optical detection of 2DEG in GaN/AlGaIn structures - High magnetic field studies. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 193-197.	0.8	1
112	ZnO and ZnO:Mn crystals obtained with the chemical vapour transport method. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 884-887.	0.8	3
113	Enhanced Zeeman effect in GGG:Mn ⁴⁺ ,Ca crystals. Chemical Physics, 2004, 298, 267-272.	0.9	5
114	The chemical vapour transport growth of ZnO single crystals. Journal of Alloys and Compounds, 2004, 371, 150-152.	2.8	34
115	Spatially Resolved Micro-Luminescence from GaN/AlGaIn Quantum Dots. Acta Physica Polonica A, 2004, 105, 517-521.	0.2	4
116	Emission from Mesoscopic-Size Islands Formed in a GaAs/AlAs Double Layer Structure. Acta Physica Polonica A, 2004, 106, 367-381.	0.2	9
117	Resonant interaction of LO phonons with excited donor states in GaN. Physica Status Solidi (B): Basic Research, 2003, 235, 36-39.	0.7	16
118	Selective magneto-luminescence spectroscopy of donoacceptor pairs in n-GaAs. Physica Status Solidi (B): Basic Research, 2003, 235, 48-53.	0.7	1
119	Fine Structure of Effective Mass Acceptors in Gallium Nitride. Physical Review Letters, 2003, 91, 226404.	2.9	25
120	Dynamics of trapping on donors and relaxation of the B-exciton in GaN. Physica Status Solidi (B): Basic Research, 2003, 235, 31-35.	0.7	4
121	Formation of Mn-Related Defect Band in InP. Acta Physica Polonica A, 2003, 103, 637-642.	0.2	3
122	Localization Effects in GaN/AlGaIn Quantum Well - Photoluminescence Studies. Acta Physica Polonica A, 2003, 103, 573-578.	0.2	1
123	Recombination of excitons bound to oxygen and silicon donors in freestanding GaN. Physical Review B, 2002, 66, .	1.1	61
124	Single-dot-like emission induced by high magnetic fields. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 876-879.	1.3	8
125	Modulation of the Yb ³⁺ to Er ³⁺ energy transfer in LiNbO ₃ crystals by applying magnetic field. Journal of Alloys and Compounds, 2001, 323-324, 344-347.	2.8	2
126	Magneto-Spectroscopy of Two-Electron Transitions in Homoepitaxial GaN.. Materials Research Society Symposia Proceedings, 2001, 693, 739.	0.1	0

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127	Inelastic light scattering on coupled plasmon-LO phonon modes in high magnetic fields. Physica B: Condensed Matter, 2001, 298, 216-220.	1.3	4
128	Symmetry of excitons in GaN. Physical Review B, 1999, 60, 4438-4441.	1.1	45
129	Spin-orbit splitting of acceptor states in Si and C. Physica B: Condensed Matter, 1999, 273-274, 640-643.	1.3	13
130	Polarised Magnetoluminescence of Excitons in Homoepitaxial GaN Layers. Physica Status Solidi (B): Basic Research, 1999, 216, 11-15.	0.7	10
131	Emission Due to Exciton Scattering by LO-Phonons in Gallium Nitride. Physica Status Solidi (B): Basic Research, 1999, 216, 95-99.	0.7	10
132	Impurity-Related Luminescence of Homoepitaxial GaN Studied with High Magnetic Fields. Physica Status Solidi (B): Basic Research, 1998, 210, 373-383.	0.7	20
133	Effects of defect scattering on the photoluminescence of exciton-polaritons in n-GaN. Solid State Communications, 1998, 105, 497-501.	0.9	17
134	Different paths to tunability in III-V quantum dots. Journal of Applied Physics, 1998, 84, 248-254.	1.1	43
135	Electrically modulated photoluminescence in self-organized InGaAs/GaAs quantum dots. Applied Physics Letters, 1998, 73, 2811-2813.	1.5	8
136	AMMONO method of BN, AlN and GaN synthesis and crystal growth.. MRS Internet Journal of Nitride Semiconductor Research, 1998, 3, 1.	1.0	41
137	Optical Properties of Self-Organized InGaAs/GaAs Quantum Dots in Field-Effect Structures. Materials Research Society Symposia Proceedings, 1998, 536, 269.	0.1	0
138	Interactions of LO Phonons with Bound Excitons in Homoepitaxial GaN. Materials Research Society Symposia Proceedings, 1997, 482, 545.	0.1	8
139	Luminescence Of A New Material: GaN Grown On NdGaO3. Materials Research Society Symposia Proceedings, 1997, 482, 748.	0.1	2
140	Observation Of Native Ga Vacancies In Gan By Positron Annihilation. Materials Research Society Symposia Proceedings, 1997, 482, 778.	0.1	17
141	Polariton effects in reflectance and emission spectra of homoepitaxial GaN. Physical Review B, 1997, 56, 15151-15156.	1.1	90
142	Observation of Native Ga Vacancies in GaN by Positron Annihilation. Physical Review Letters, 1997, 79, 3030-3033.	2.9	459
143	Two-Electron Transition in Homoepitaxial GaN Layers. Acta Physica Polonica A, 1997, 92, 742-744.	0.2	12
144	Structural and Optical Properties of Homoepitaxial GaN Layers. Materials Research Society Symposia Proceedings, 1996, 449, 393.	0.1	27

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145	Luminescence and reflectivity in the exciton region of homoepitaxial GaN layers grown on GaN substrates. <i>Solid State Communications</i> , 1996, 97, 919-922.	0.9	130
146	Shallow Donors and Acceptors in GaN; Bound Excitons and Pair Spectra. <i>Acta Physica Polonica A</i> , 1996, 90, 681-690.	0.2	14
147	Coupling of LO Phonons to Excitons in GaN. <i>Acta Physica Polonica A</i> , 1996, 90, 981-984.	0.2	1
148	Growth and Properties of Bulk Single Crystals of GaN. <i>Materials Research Society Symposia Proceedings</i> , 1995, 395, 15.	0.1	6
149	Competition of Radiation Processes in 6H-SiC Observed by Luminescence. <i>Acta Physica Polonica A</i> , 1995, 87, 437-440.	0.2	3
150	GaN Synthesis by Ammonothermal Method. <i>Acta Physica Polonica A</i> , 1995, 88, 833-836.	0.2	76
151	Growth of GaN Metalorganic Chemical Vapour Deposition Layers on GaN Single Crystals. <i>Acta Physica Polonica A</i> , 1995, 88, 861-864.	0.2	1
152	Orientation of Metastable EL2 under Uniaxial Stress. <i>Acta Physica Polonica A</i> , 1995, 87, 137-140.	0.2	0
153	Influence of Impact Ionization of Shallow Donors on Luminescence in GaAs. <i>Acta Physica Polonica A</i> , 1995, 87, 261-264.	0.2	0
154	GaN Layers Grown by Reactive Ion Plating. <i>Acta Physica Polonica A</i> , 1995, 88, 1058-1062.	0.2	0
155	Origin of Centres Involved in Blue and Orange Luminescence of 6H-SiC. <i>Acta Physica Polonica A</i> , 1995, 88, 957-960.	0.2	0
156	Large negative persistent photoconductivity of bulk GaAs _{1-x} P _x () single crystals. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1993, 21, 325-328.	1.7	0
157	Deep Level Transient Spectroscopy Measurements of an Acceptor-like State of Metastable EL2 in GaAs and GaAsP. <i>Acta Physica Polonica A</i> , 1993, 84, 673-676.	0.2	0
158	Optical and Electrical Measurements of Low-Temperature InAlAs. <i>Acta Physica Polonica A</i> , 1992, 82, 825-828.	0.2	2
159	"Excitonic" and Photoionization Absorption Spectra of Iron in III-V Materials. <i>Acta Physica Polonica A</i> , 1992, 82, 911-913.	0.2	3
160	Optical and Electrical Studies of FR1 and FR2 Defects in GaAs. <i>Acta Physica Polonica A</i> , 1992, 82, 613-616.	0.2	0
161	Electrical Properties of an Acceptor-like State of Metastable EL2 in n-type GaAs under Uniaxial Stress. <i>Acta Physica Polonica A</i> , 1992, 82, 908-910.	0.2	0
162	Hydrostatic Pressure Spectroscopy of the Vanadium Luminescence in GaAs. <i>Acta Physica Polonica A</i> , 1992, 82, 837-840.	0.2	0

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163	Homoepitaxy of GaN - growth, investigations and applications. , 0, , .		0
164	Growth of Graphene Layers on Silicon Carbide. Materials Science Forum, 0, 615-617, 199-202.	0.3	15
165	Growth Rate and Thickness Uniformity of Epitaxial Graphene. Materials Science Forum, 0, 645-648, 569-572.	0.3	7